



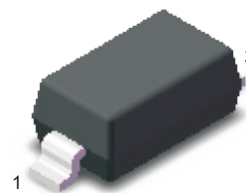
1N4148WA

Silicon Epitaxial Planar Switching Diode

Features

- For surface mounted applications
- Fast reverse recovery time
- Ideal for automated placement

SOD-123W



1.Cathode —|<— 2.Anode

Marking Code: T4

Absolute Maximum Ratings at $T_A = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	1N4148WA	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum RMS voltage	V_{RMS}	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ s}$ at $t = 1\text{ ms}$ at $t = 1\text{ }\mu\text{s}$	I_{FSM}	0.5 1 4	A
Maximum Power Dissipation	P_D	400	mW
Operating Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$

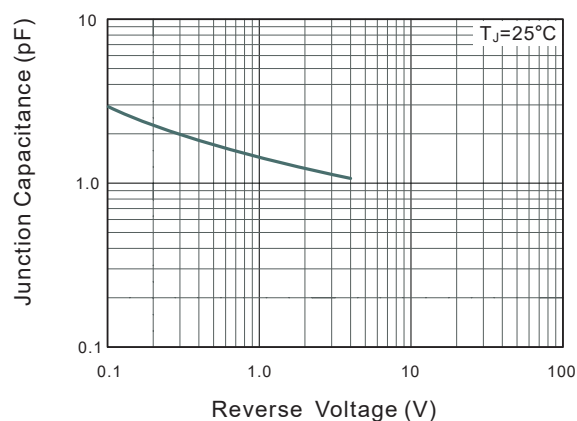
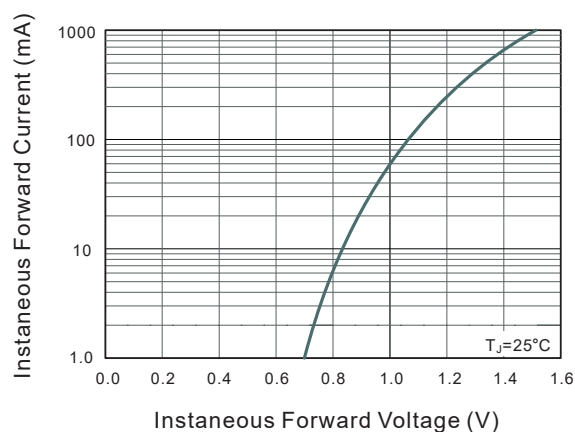
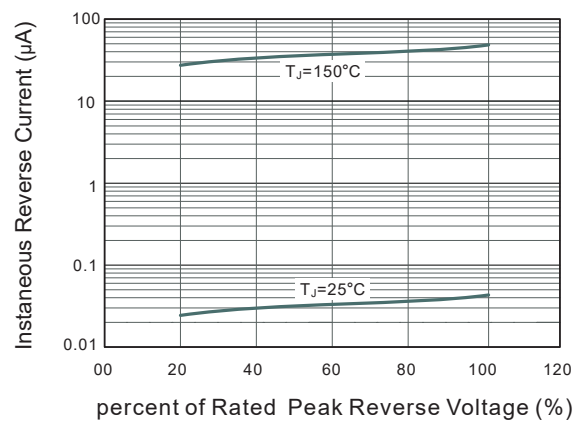
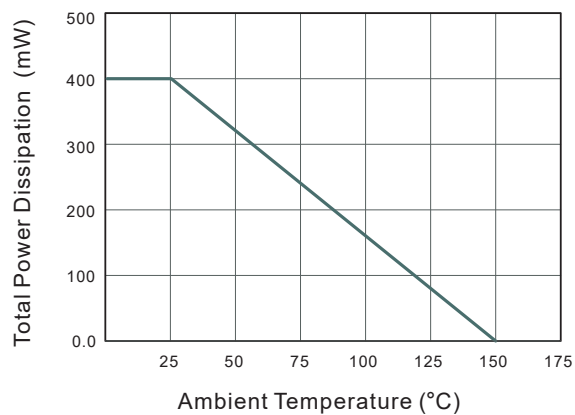
Parameter	Symbol	1N4148WA	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ }\mu\text{A}$	$V_{(BR)R}$	75	V
Maximum Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1.00 1.25	V
Peak Reverse Current at $V_R = 20\text{ V}, T_J = 25\text{ }^{\circ}\text{C}$ at $V_R = 75\text{ V}, T_J = 25\text{ }^{\circ}\text{C}$ at $V_R = 25\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$ at $V_R = 75\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$	I_R	0.025 1 30 50	μA
Typical Junction Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R, I_F = I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$	T_{rr}	4	nS



1N4148WA

Silicon Epitaxial Planar Switching Diode

Typical Characteristic Curves





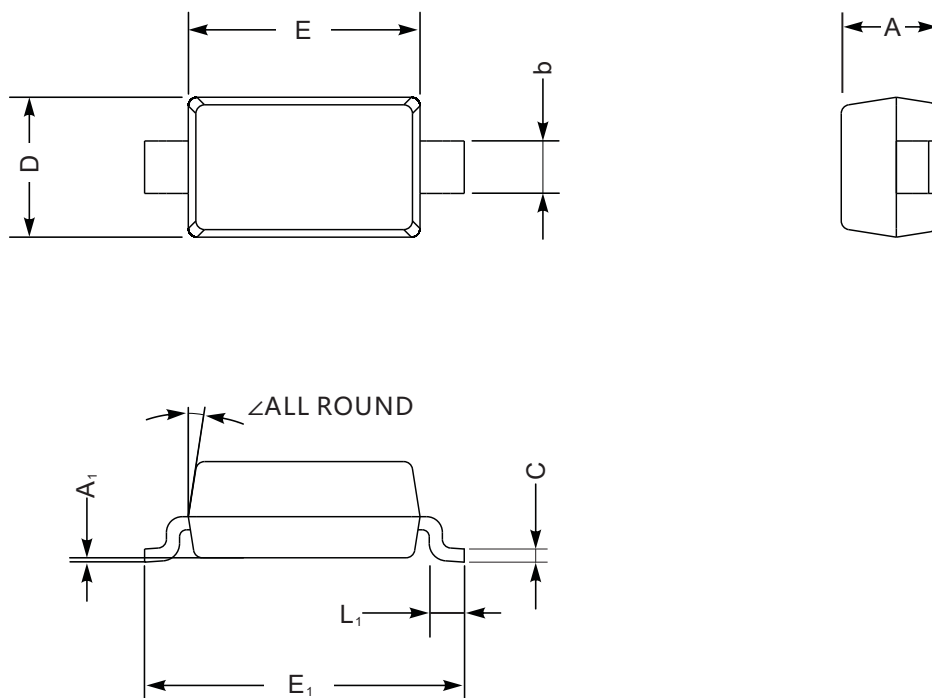
1N4148WA

Silicon Epitaxial Planar Switching Diode

Package Outline

SOD-123W

Dimensions in mm



UNIT		A	C	D	E	E ₁	L ₁	b	A ₁	∠
mm	max	1.3	0.22	1.8	2.8	3.9	0.45	0.7	0.2	9°
	min	0.9	0.09	1.5	2.5	3.6	0.25	0.5	—	
mil	max	51	8.7	71	110	154	18	28	8	
	min	35	3.5	59	98	142	10	20	—	